

AMENDMENT TO THE CLAIMS

IN THE CLAIMS:

Please **AMEND** claims 1-14, 18 and 27; and

Please **ADD** claim 28 as follows.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A device, comprising:
an active region including a collector region;
an oxide layer ~~formed over~~ arranged on one side of the collector region and having a conductive pathway in electrical contact with the collector region; and
a collector metal contact ~~deposited~~ arranged over the oxide layer and the conductive pathway; and
an emitter region arranged on another side of the collector region and in the active region,
wherein the conductive pathway through the oxide layer provides electrical contact between the collector metal contact and the collector region.
2. (Currently Amended) The ~~structure~~ device of claim 1, wherein ~~the active region includes an emitter region;~~ a base region ~~deposited~~ is arranged on a top surface of the emitter region, and the collector region ~~deposited~~ is arranged on a top surface of the base region.
3. (Currently Amended) The ~~structure~~ device of claim 2, further comprising a passivation layer ~~deposited~~ arranged about the emitter region and about the base

region, and a second oxide layer ~~deposited~~ disposed around a side of the collector region and in contact with the oxide layer.

4. (Currently Amended) The ~~structure~~ device of claim 1, wherein the conductive pathway through the oxide layer from the collector metal contact to the collector region comprises a vertical conductive pathway.

5. (Currently Amended) The ~~structure~~ device of claim 1, wherein the conductive pathway through the oxide layer from the collector metal contact to the collector region comprises a metal filled via.

6. (Currently Amended) The ~~structure~~ device of claim 1, further comprising a silicide layer disposed between a surface of the collector region and the oxide layer.

7. (Currently Amended) The ~~structure~~ device of claim 1, wherein the conductive pathway to the collector region comprises a base metal contact disposed on a top of the oxide layer.

8. (Currently Amended) The ~~structure~~ device of claim 7, further comprising a further conductive pathway to at least one of a base region and the emitter region.

9. (Currently Amended - Withdrawn) The ~~structure~~ device of claim 8, wherein the further conductive pathway includes a first conductive pathway and a second

conductive pathway, wherein the first conductive pathway comprises filled vias ~~formed~~ arranged in the oxide layer, the second oxide layer and the passivation layer and between metal contacts and the emitter region, wherein the second conductive pathway includes a filled via ~~formed~~ arranged in the oxide layer and the second oxide layer and between a metal contact and the base region.

10. (Currently Amended - Withdrawn) The ~~structure~~ device of claim 8, wherein the first conductive pathway is ~~formed~~ arranged in the oxide layer, the second oxide and the passivation layer.

11. (Currently Amended - Withdrawn) The ~~structure~~ device of claim 10, wherein the first conductive pathway includes filled vias ~~formed~~ arranged in the oxide layer and the second oxide layer and the passivation layer, and between metal contacts and the emitter region, wherein the second conductive pathway includes a filled via ~~formed~~ arranged in the oxide layer and the second oxide layer and between a metal contact and the base region.

12. (Currently Amended - Withdrawn) The ~~structure~~ device of claim 10, wherein the second conductive pathway includes filled vias disposed within the oxide layer and the second oxide layer between a base metal contact and the base region and the emitter region.

13. (Currently Amended) A semiconductor device, comprising:
an emitter region;
a base region laying on a surface of the emitter region;

a passivation layer ~~deposited~~ disposed about the emitter region and about an edge of the base region;

a collector region laying on the base region and electrically isolated from a substrate; and

an oxide layer ~~deposited~~ disposed about at least one side and on a surface of the collector region.

14. (Currently Amended) The semiconductor device of claim 13, further comprising:

a conductive pathway to the collector region within a portion of the oxide layer ~~formed~~ arranged on top of the collector region; and

a metal contact ~~formed~~ arranged on the oxide layer and the conductive pathway to provide electrical contact to the collector region.

15. (Previously Presented) The semiconductor device of claim 13, further comprising a conductive pathway to the base region through the passivation layer.

16. (Previously Presented) The semiconductor device of claim 15, wherein the conductive pathway to the base region comprises a base metal contact on a top of the oxide layer and a filled via through the oxide layer between a base metal contact and a extrinsic base region.

17. (Withdrawn) The semiconductor device of claim 13, further comprising a conductive pathway to the emitter region including a conductive pathway through the oxide layer and the passivation layer.

18. (Currently Amended) The semiconductor device of claim 13, wherein the oxide layer comprises a first oxide layer ~~deposited~~ disposed about at least one side of the collector region and a second oxide layer ~~deposited~~ disposed on a top surface of the collector region.

Claims 19-26 (Canceled).

27. (Currently Amended) The semiconductor device of claim 13, wherein the surface of the collector region which is ~~deposited with the oxide layer~~ is opposite a side of the collector region that faces the emitter region.

28. (New) A semiconductor device, comprising:
an active region including a collector region;
an oxide layer arranged on one side of the collector region and having a conductive pathway in electrical contact with the collector region;
oxide regions disposed against side edges of the collector region;
a collector metal contact arranged over the oxide layer and the conductive pathway;
at least one of a silicide layer and a second oxide layer arranged between the one side of the collector region and the collector metal contact; and
an emitter region arranged on another side of the collector region,
wherein the conductive pathway through the oxide layer provides electrical contact between the collector metal contact and the collector region.